

# Gunnar Kusch

## List of Publications by Year in descending order

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36  
papers

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citations

840119

11  
h-index

676716

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g-index

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docs citations

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times ranked

845  
citing authors

#	ARTICLE	IF	CITATIONS
1	Carrier dynamics at trench defects in InGaN/GaN quantum wells revealed by time-resolved cathodoluminescence. <i>Nanoscale</i> , 2022, 14, 402-409.	2.8	13
2	Defect characterization of {101 $\bar{1}$ 3} GaN by electron microscopy. <i>Journal of Applied Physics</i> , 2022, 131, .	1.1	5
3	Optical emission from focused ion beam milled halide perovskite device cross-sections. <i>Microscopy Research and Technique</i> , 2022, 85, 2351-2355.	1.2	7
4	Decreased Fast Time Scale Spectral Diffusion of a Nonpolar InGaN Quantum Dot. <i>ACS Photonics</i> , 2022, 9, 275-281.	3.2	3
5	The influence of threading dislocations propagating through an AlGaIn UVC LED. <i>Applied Physics Letters</i> , 2022, 120, .	1.5	6
6	X-ray characterisation of the basal stacking fault densities of (112 $\bar{1}$ ,2) GaN. <i>CrystEngComm</i> , 2021, 23, 6059-6069.	1.3	4
7	Point Defects in InGaIn/GaN Core-Shell Nanorods: Role of the Regrowth Interface. <i>Nano Express</i> , 2021, 2, 014005.	1.2	4
8	Using pulsed mode scanning electron microscopy for cathodoluminescence studies on hybrid perovskite films. <i>Nano Express</i> , 2021, 2, 024002.	1.2	10
9	Over 15% efficient wide-band-gap Cu(In,Ga)S <sub>2</sub> solar cell: Suppressing bulk and interface recombination through composition engineering. <i>Joule</i> , 2021, 5, 1816-1831.	11.7	36
10	Multimicroscopy of cross-section zincblende GaN LED heterostructure. <i>Journal of Applied Physics</i> , 2021, 130, .	1.1	6
11	Understanding the Role of Grain Boundaries on Charge-Carrier and Ion Transport in Cs <sub>2</sub> AgBiBr <sub>6</sub> Thin Films. <i>Advanced Functional Materials</i> , 2021, 31, 2104981.	7.8	39
12	A systematic comparison of polar and semipolar Si-doped AlGaIn alloys with high AlN content. <i>Journal Physics D: Applied Physics</i> , 2021, 54, 035302.	1.3	9
13	AlN overgrowth of nano-pillar-patterned sapphire with different offcut angle by metalorganic vapor phase epitaxy. <i>Journal of Crystal Growth</i> , 2020, 531, 125343.	0.7	13
14	Efficient light-emitting diodes from mixed-dimensional perovskites on a fluoride interface. <i>Nature Electronics</i> , 2020, 3, 704-710.	13.1	143
15	Stacking fault-associated polarized surface-emitted photoluminescence from zincblende InGaIn/GaN quantum wells. <i>Applied Physics Letters</i> , 2020, 117, .	1.5	6
16	Advances in electron channelling contrast imaging and electron backscatter diffraction for imaging and analysis of structural defects in the scanning electron microscope. <i>IOP Conference Series: Materials Science and Engineering</i> , 2020, 891, 012023.	0.3	0
17	Metrology of crystal defects through intensity variations in secondary electrons from the diffraction of primary electrons in a scanning electron microscope. <i>Ultramicroscopy</i> , 2020, 213, 112977.	0.8	2
18	Structural and luminescence imaging and characterisation of semiconductors in the scanning electron microscope. <i>Semiconductor Science and Technology</i> , 2020, 35, 054001.	1.0	7

#	ARTICLE	IF	CITATIONS
19	Halide Homogenization for High-Performance Blue Perovskite Electroluminescence. <i>Research</i> , 2020, 2020, 9017871.	2.8	32
20	Influence of InN and AlN concentration on the compositional inhomogeneity and formation of InN-rich regions in $\text{In}_x\text{Al}_y\text{Ga}_{1-x-y}\text{N}$ . <i>Japanese Journal of Applied Physics</i> , 2019, 58, SCCB18.	0.8	3
21	Indium incorporation in quaternary $\text{In}_x\text{Al}_y\text{Ga}_{1-x-y}\text{N}$ for UVB-LEDs. <i>Japanese Journal of Applied Physics</i> , 2019, 58, SC1004.	0.8	5
22	Scanning electron microscopy as a flexible technique for investigating the properties of UV-emitting nitride semiconductor thin films. <i>Photonics Research</i> , 2019, 7, B73.	3.4	9
23	Multi-wavelength emission from a single InGaN/GaN nanorod analyzed by cathodoluminescence hyperspectral imaging. <i>Scientific Reports</i> , 2018, 8, 1742.	1.6	9
24	Hybrid Top-Down/Bottom-Up Fabrication of Regular Arrays of AlN Nanorods for Deep-UV Core-Shell LEDs. <i>Physica Status Solidi (B): Basic Research</i> , 2018, 255, 1700445.	0.7	14
25	You Do What in Your Microprobe?! The EPMA as a Multimode Platform for Nitride Semiconductor Characterization. <i>Microscopy and Microanalysis</i> , 2018, 24, 2026-2027.	0.2	1
26	Hybrid Top-Down/Bottom-Up Fabrication of a Highly Uniform and Organized Faceted AlN Nanorod Scaffold. <i>Materials</i> , 2018, 11, 1140.	1.3	10
27	Deep UV Emission from Highly Ordered AlGaN/AlN Core-Shell Nanorods. <i>ACS Applied Materials &amp; Interfaces</i> , 2018, 10, 33441-33449.	4.0	29
28	Analysis of doping concentration and composition in wide bandgap AlGaN:Si by wavelength dispersive x-ray spectroscopy. <i>Semiconductor Science and Technology</i> , 2017, 32, 035020.	1.0	13
29	Optical properties and resonant cavity modes in axial InGaN/GaN nanotube microcavities. <i>Optics Express</i> , 2017, 25, 28246.	1.7	22
30	Correction: Site controlled red-yellow-green light emitting InGaN quantum discs on nano-tipped GaN rods. <i>Nanoscale</i> , 2016, 8, 13521-13521.	2.8	0
31	Self-Healing Thermal Annealing: Surface Morphological Restructuring Control of GaN Nanorods. <i>Crystal Growth and Design</i> , 2016, 16, 6769-6775.	1.4	10
32	Site controlled red-yellow-green light emitting InGaN quantum discs on nano-tipped GaN rods. <i>Nanoscale</i> , 2016, 8, 11019-11026.	2.8	12
33	Spatial clustering of defect luminescence centers in Si-doped low resistivity Al <sub>0.82</sub> Ga <sub>0.18</sub> N. <i>Applied Physics Letters</i> , 2015, 107, .	1.5	22
34	Influence of substrate miscut angle on surface morphology and luminescence properties of AlGaN. <i>Applied Physics Letters</i> , 2014, 104, 092114.	1.5	24
35	Electron Channeling Contrast Imaging of Defects in III-Nitride Semiconductors. <i>Microscopy and Microanalysis</i> , 2014, 20, 1024-1025.	0.2	0
36	Cathodoluminescence Hyperspectral Imaging of Nitride Semiconductors: Introducing New Variables. <i>Microscopy and Microanalysis</i> , 2014, 20, 906-907.	0.2	0